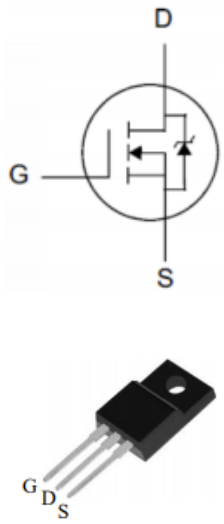
XTMF65N07F

650V N-ch Planar MOSFET

Product Description

BV_{DSS}	650	V
I_D	7.0	A
$R_{DS(ON),Typ.}$	1.2	Ω

封装 **Package**



General Features

- RoHS Compliant
- $R_{DS(ON),typ.}$=1.2 Ω@V_{GS}=10V
- Fast Recovery Body Diode
- Low Gate Charge Minimize Switching Loss

Applications

- Adaptor
- Charger
- SMPS Standby Power

Device	Package	Marking
XTMF65N07F	TO-220F	XTMF65N07F

Absolute Maximum Ratings T_j=25℃

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-to-Source Voltage	650	V
V_{GSS}	Gate-to-Source Voltage	±30	
I_D	Continuous Drain Current	7.0	A
I_{DM}	Pulsed Drain Current at V_{GS}=10V	28	
E_{AS}	Single Pulse Avalanche Energy	550	mJ
P_D	Power Dissipation	42	W
	Derating Factor above 25℃	0.34	W/℃
T_L T_{PAK}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	℃
T_J& T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the “Absolute Maximum Ratings” may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	Value	Unit
		XTMF65N07F	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.98	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	100	℃/W

Electrical Characteristics T_j=25℃

OFF Characteristics

Symbol	Parameter	Min	Typ	Max	Unit	Test Condition
BV_{DSS}	Drain-to-Source Breakdown Voltage	650	-	-	V	V_{GS}=0V, I_D=250uA
I_{DSS}	Drain-to-Source Leakage Current	-	-	1	uA	V_{DS}=650V, V_{GS}=0V
		-	-	100		V_{DS}=520V, V_{GS}=0V, T_J=125℃
I_{GSS}	Gate-to-Source Leakage Current	-	-	+100	nA	V_{GS}=+30V, V_{DS}=0V
		-	-	-100		V_{GS}=-30V, V_{DS}=0V

ON Characteristics

Symbol	Parameter	Min	Typ	Max	Unit	Test Condition
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	-	1.2	1.4	Ω	V_{GS}=10V, I_D=3.0A
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	-	4.0	V	V_{DS}=V_{GS}, I_D=250uA
gfs	Forward Transconductance	-	11	-	S	V_{DS}=30V,I_D=3.5A

Dynamic Characteristics

Symbol	Parameter	Min	Typ	Max	Unit	Test Condition
C_{iss}	Input Capacitance	-	1120	-	pF	V_{GS}=0V, V_{DS}=25V, f=1.0MH$_Z$
C_{rss}	Reverse Transfer Capacitance	-	10	-		
C_{oss}	Output Capacitance	-	90	-		
Q_g	Total Gate Charge	-	20	-	nC	V_{DD}=325V, I_D=7A, V_{GS}=0 to 10V
Q_{gs}	Gate-to-Source Charge	-	5	-		
Q_{gd}	Gate-to-Drain (Miller) Charge	-	5	-		

Resistive Switching Characteristics

Symbol	Parameter	Min	Typ	Max	Unit	Test Condition
$td_{(ON)}$	Turn-on Delay Time	-	12	-	ns	V_{DD}=325V, I_D=7A, V_{GS}=10V Rg=4.7Ω
t_{rise}	Rise Time	-	12	-		
$td_{(OFF)}$	Turn-Off Delay Time	-	18	-		
t_{fall}	Fall Time	-	10	-		

Source-Drain Body Diode Characteristics

Symbol	Parameter	Min	Typ	Max	Unit	Test Condition
I_{SD}	Continuous Source Current[1]	-	-	7.0	A	Integral pn-diode in MOSFET
I_{SM}	Pulsed Source Current[1]	-	-	28		
V_{SD}	Diode Forward Voltage	-	-	1.5	V	I_S=7A, V_{GS}=0V
t_{rr}	Reverse Recovery Time	-	350	-	ns	V_{GS}=0V I_F=7A, di/dt=100A/μs
Q_{rr}	Reverse Recovery Charge	-	1.1	-	uC	

[1] Pulse width≤380μs; duty cycle≤2%

Typical Characteristics

Figure 1. Maximum Effective Thermal Impedance, Junction-to-Case

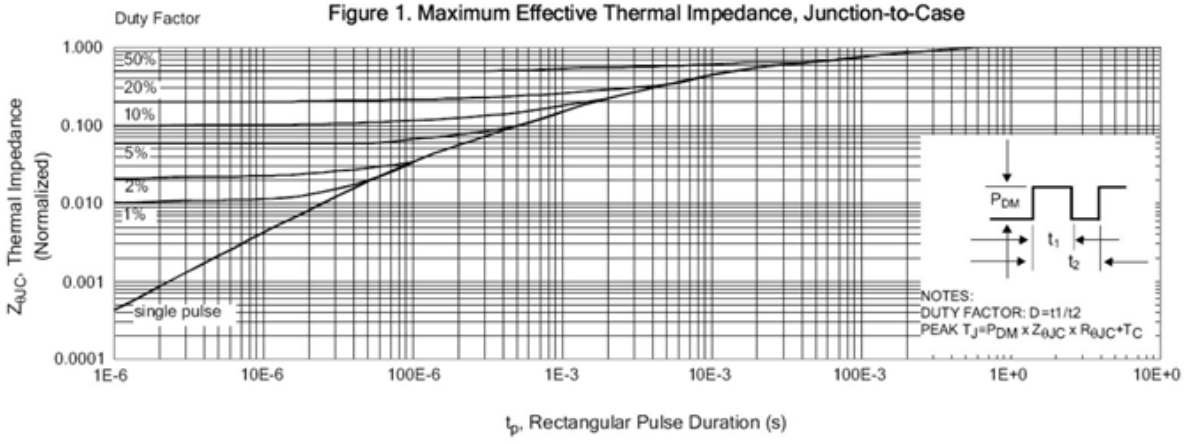


Figure 2. Maximum Power Dissipation vs Case Temperature

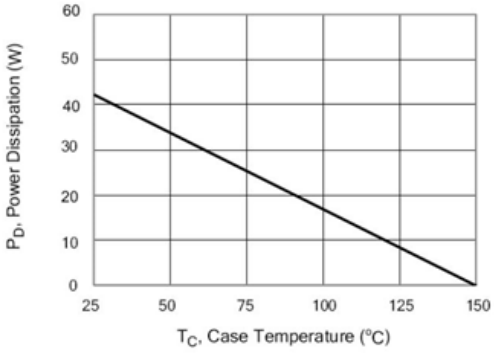


Figure 3. Maximum Continuous Drain Current vs Case Temperature

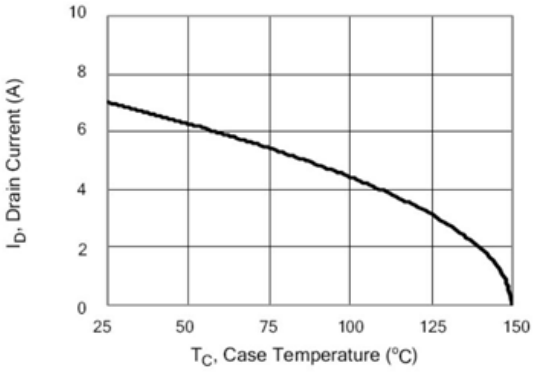


Figure 4. Typical Output Characteristics

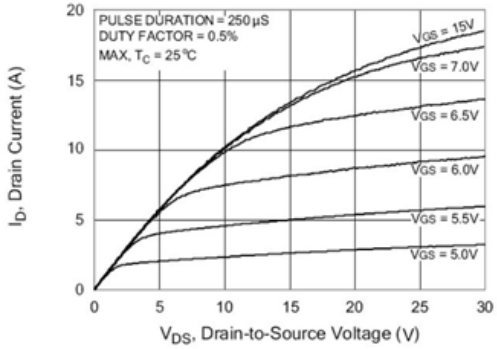
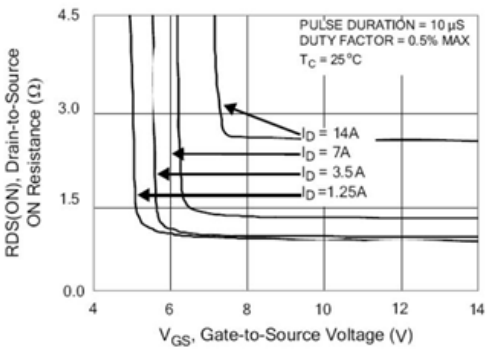


Figure 5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current



Typical Characteristics(Cont.)

Figure 6. Maximum Peak Current Capability

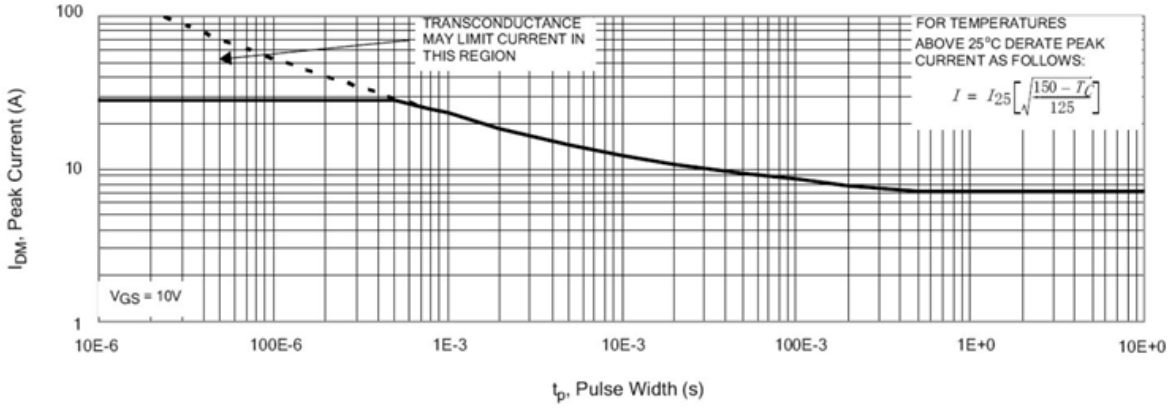


Figure 7. Typical Transfer Characteristics

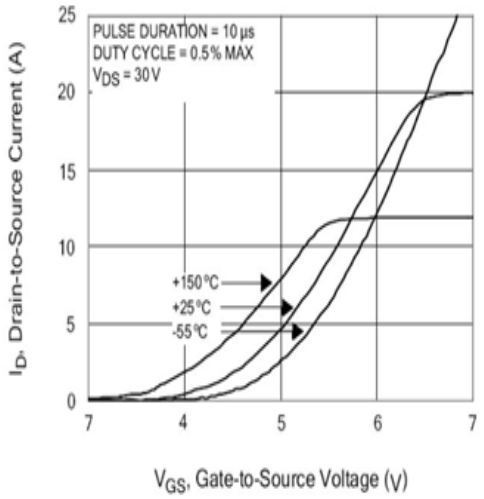


Figure 8. Unclamped Inductive Switching Capability

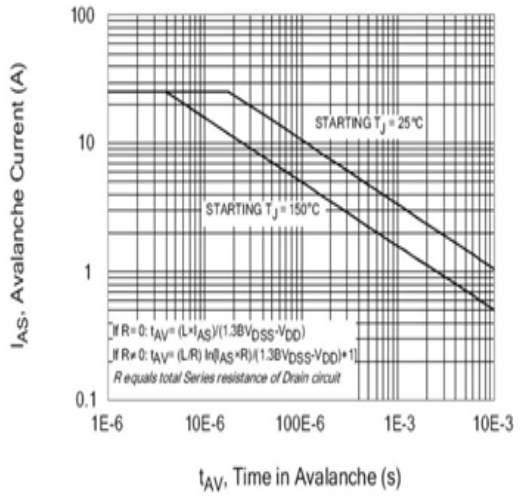


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

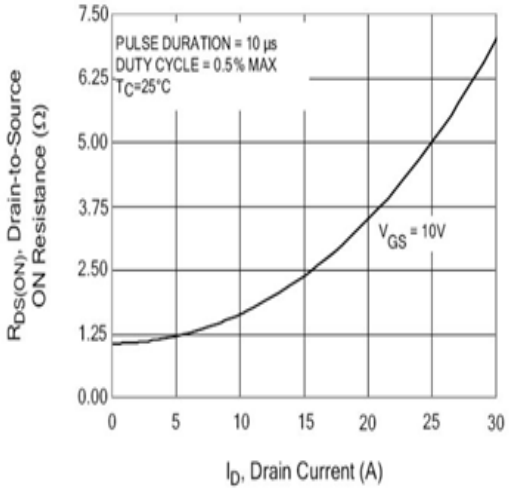
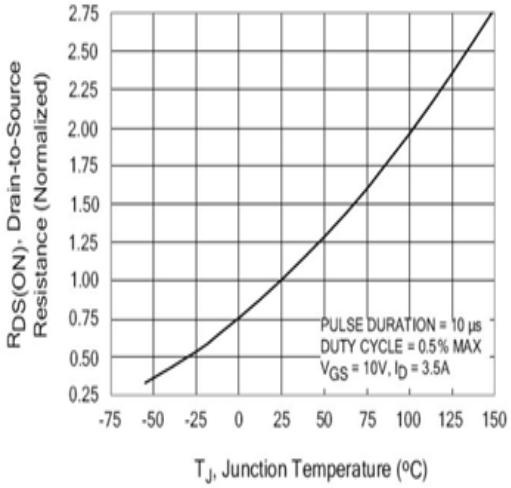


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature



Typical Characteristics(Cont.)

Figure 11. Typical Breakdown Voltage vs Junction Temperature

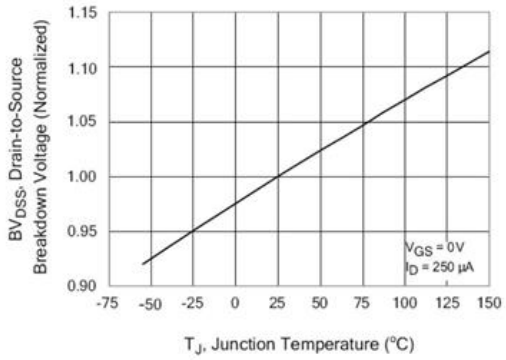


Figure 12. Typical Threshold Voltage vs Junction Temperature

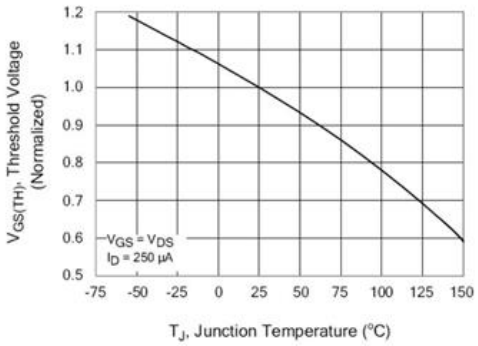


Figure 13 . Maximum Safe Operating Area

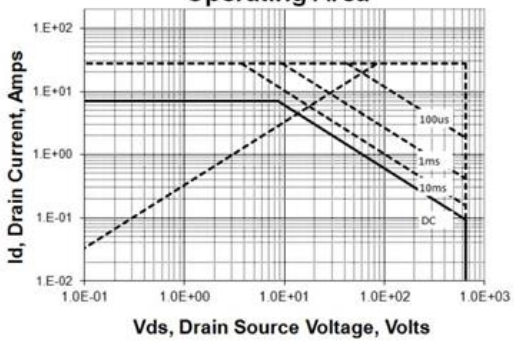


Figure 14. Capacitance vs Vds

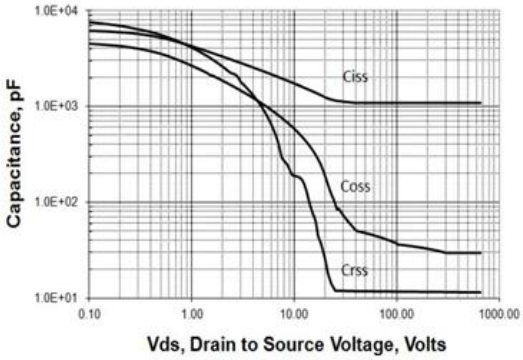


Figure 15 . Typical Gate Charge

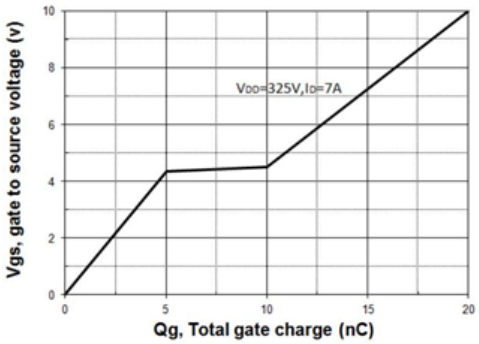
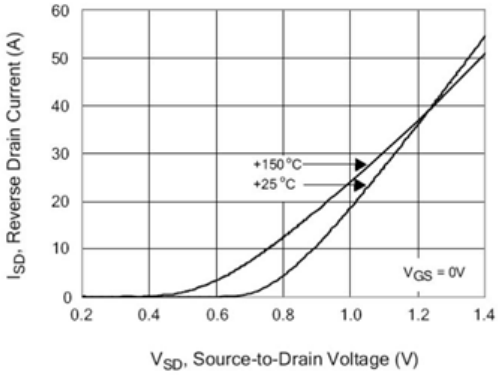


Figure 16. Typical Body Diode Transfer Characteristics



Typical Characteristics(Cont.)

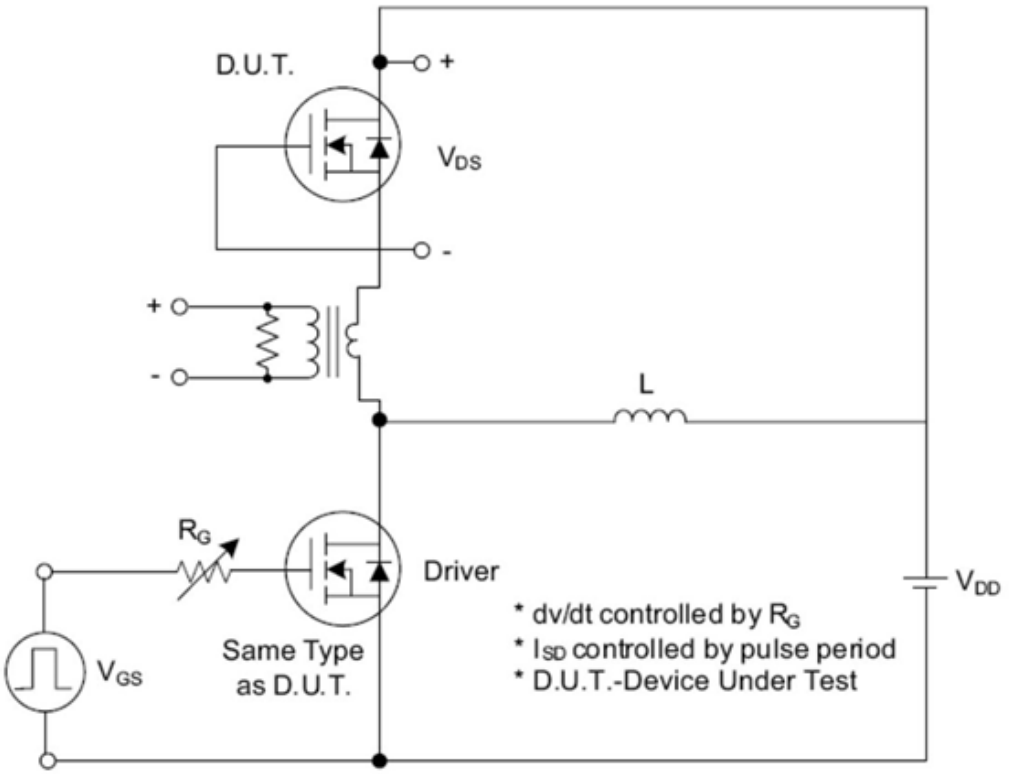


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

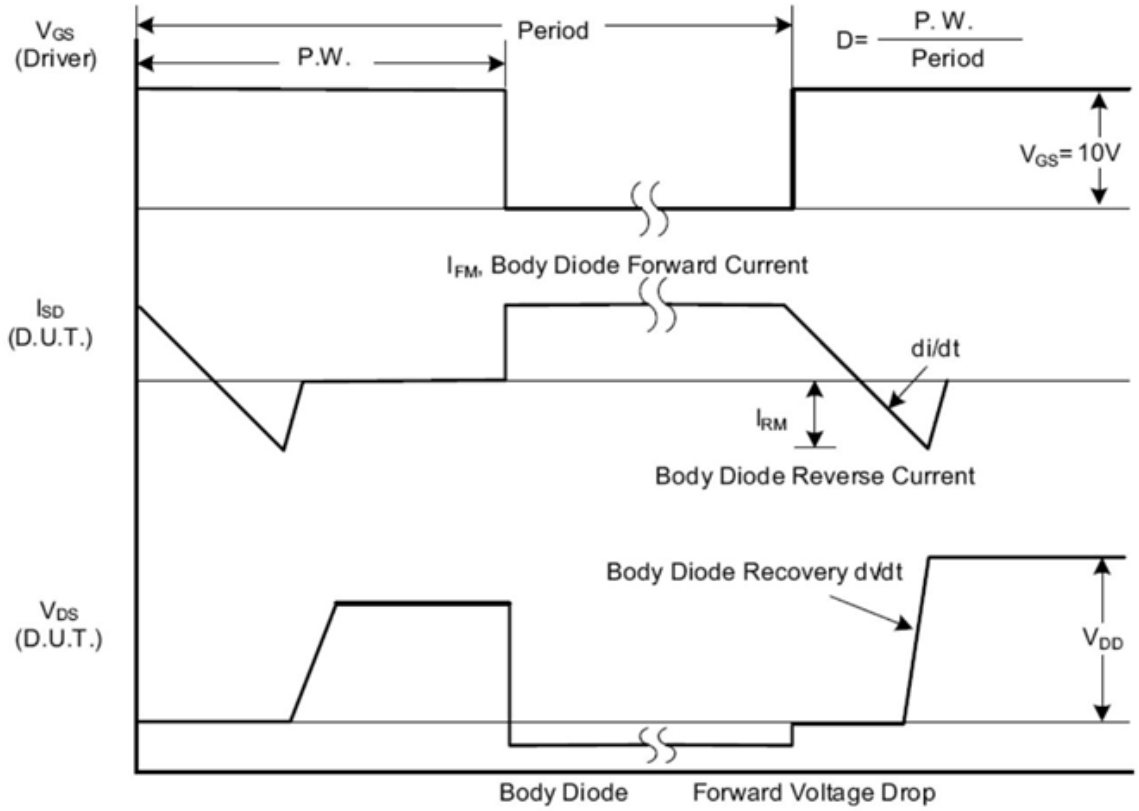


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms

Test Circuits and Waveforms (Cont.)

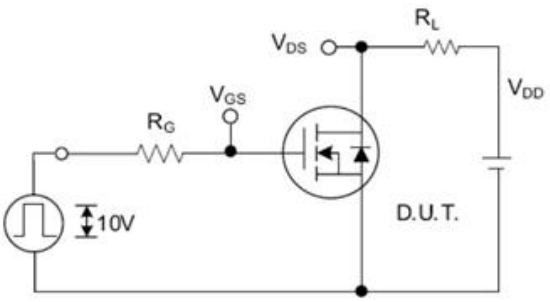


Fig. 2.1 Switching Test Circuit

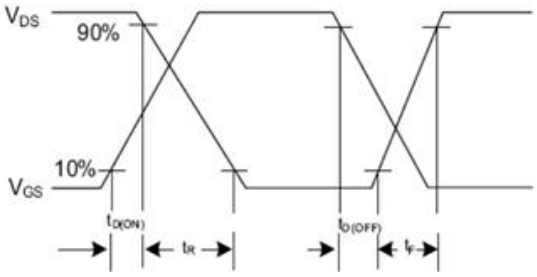


Fig. 2.2 Switching Waveforms

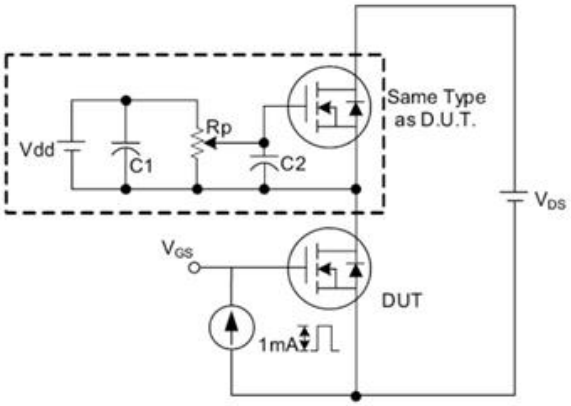


Fig. 3 . 1 Gate Charge Test Circuit

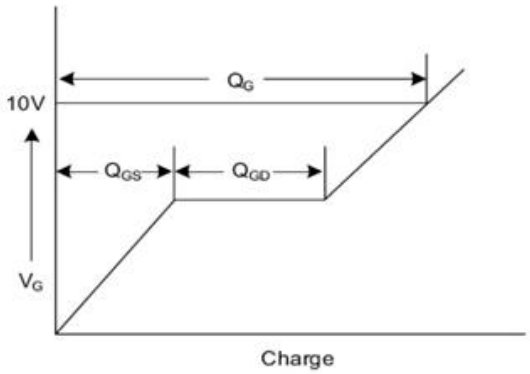


Fig. 3 . 2 Gate Charge Waveform

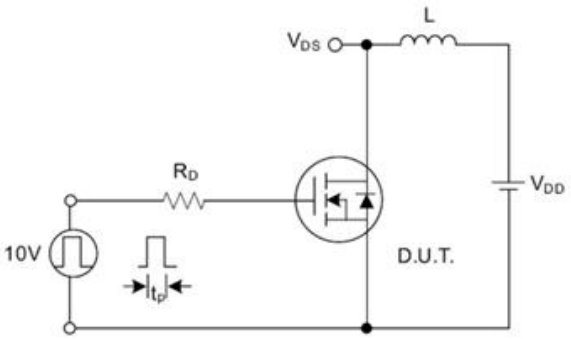


Fig. 4.1 Unclamped Inductive Switching Test Circuit

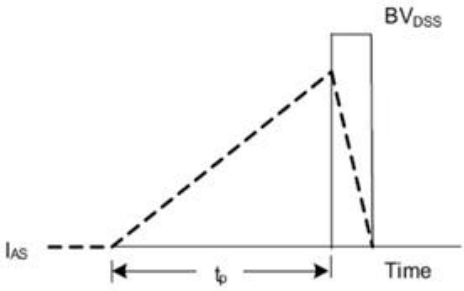


Fig. 4.2 Unclamped Inductive Switching Waveforms